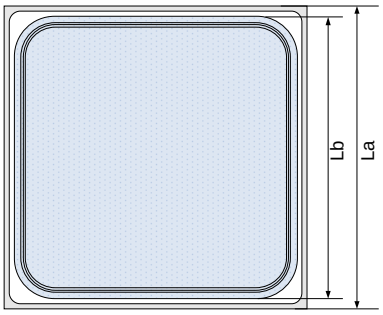
2SB083060ML SCHOTTKY BARRIER DIODE CHIPS

DESCRIPTION

- Ø 2SB083060ML is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits.;
- Ø Chip Size:830μm X 830μm;
- Ø Chip Thickness: 280±20μm;



Chip Topography and Dimensions

La: Chip Size: 830μm;

Lb: Pad Size: 670μm;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB083060MLYY	For axial leads package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	60	V
Average Forward Rectified Current	I_{FAV}	1	A
Peak Forward Surge Current@8.3ms	I_{FSM}	30	A
Maximum Operation Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{STG}	-40~125	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25**°C**)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	V_{BR}	I_R=1mA	60	--	V
Forward Voltage	V_F	I_F=1A	--	0.70	V
Reverse Current	I_R	V_R=60V	--	1	mA